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PREPARATION AND PROPERTIES OF ((TRIMETHYLSILYL)-METHYL)-GALLIUM--ETC(U)
NOV 79 O T BEACHLEY, R G SIMMONS

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was prepared from GaCl_3 by a standard Grignard reaction in diethylether. The halogen derivatives were prepared from $\text{Ga}(\text{CH}_2\text{SiMe}_3)_3$ by elimination reactions with HCl or HBr and exchange reactions with GaCl_3 or GaBr_3 . The following molecular formulas are supported by all available data: $\text{Ga}(\text{CH}_2\text{SiMe}_3)_3$, $[\text{Ga}(\text{CH}_2\text{SiMe}_3)_2\text{Cl}]_x$, $[\text{Ga}(\text{CH}_2\text{SiMe}_3)_2\text{Br}]_2$, $[\text{Ga}(\text{CH}_2\text{SiMe}_3)\text{Cl}_2]_2$ and $[\text{Ga}(\text{CH}_2\text{SiMe}_3)\text{Br}_2]_2$. It is noteworthy that the (trimethylsilyl)methyl ligand significantly influences the chemistry of only $\text{Ga}(\text{CH}_2\text{SiMe}_3)_3$ and $[\text{Ga}(\text{CH}_2\text{SiMe}_3)_2\text{Cl}]_x$. The Lewis acidity of $\text{Ga}(\text{CH}_2\text{SiMe}_3)_3$ has been greatly diminished as diethylether can be readily removed by simple vacuum distillation. The chemical and physical properties of $\text{Ga}(\text{CH}_2\text{SiMe}_3)_2\text{Cl}$, which could only be prepared in low yield by the elimination reaction, suggest that the compound might have an unusual structure. A "ladder" polymer or a linear polymer with one bridging chlorine atom per gallium atom is proposed. All other ((trimethylsilyl)methyl)gallium halogen compounds have properties analogous with other known organogallium halogen compounds.

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Preparation and Properties of ((Trimethylsilyl)methyl)-
gallium(III) Compounds

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Abstract

A series of neutral organogallium(III) compounds which incorporate the (trimethylsilyl)methyl ligand, $\text{Ga}(\text{CH}_2\text{SiMe}_3)_n \text{X}_{3-n}$ ($n = 3, 2, 1$; $\text{X} = \text{Cl}, \text{Br}$) have been prepared and fully characterized by elemental analyses, ^1H NMR and infrared spectroscopy, molecular weight data, solubility properties and Lewis acid-base chemistry. The parent compound $\text{Ga}(\text{CH}_2\text{SiMe}_3)_3$ was prepared from GaCl_3 by a standard Grignard reaction in diethylether. The halogen derivatives were prepared from $\text{Ga}(\text{CH}_2\text{SiMe}_3)_3$ by elimination reactions with HCl or HBr and exchange reactions with GaCl_3 or GaBr_3 . The following molecular formulas are supported by all available data: $\text{Ga}(\text{CH}_2\text{SiMe}_3)_3$, $[\text{Ga}(\text{CH}_2\text{SiMe}_3)_2\text{Cl}]_x$, $[\text{Ga}(\text{CH}_2\text{SiMe}_3)_2\text{Br}]_2$, $[\text{Ga}(\text{CH}_2\text{SiMe}_3)\text{Cl}_2]_2$ and $[\text{Ga}(\text{CH}_2\text{SiMe}_3)\text{Br}_2]_2$. It is noteworthy that the (trimethylsilyl)methyl ligand significantly influences the chemistry of only $\text{Ga}(\text{CH}_2\text{SiMe}_3)_3$ and $[\text{Ga}(\text{CH}_2\text{SiMe}_3)_2\text{Cl}]_x$. The Lewis acidity of $\text{Ga}(\text{CH}_2\text{SiMe}_3)_3$ has been greatly diminished as diethylether can be readily removed by simple vacuum distillation. The chemical and physical properties of $\text{Ga}(\text{CH}_2\text{SiMe}_3)_2\text{Cl}$, which could only be prepared in low yield by the elimination reaction, suggest that the compound might have an unusual structure. A "ladder"

polymer or a linear polymer with one bridging chlorine atom per gallium atom is proposed. All other ((trimethylsilyl)methyl)gallium halogen compounds have properties analogous with other known organogallium halogen compounds.

Introduction

The enhanced thermal stability of the ((trimethylsilyl)methyl)metal compounds and their potential for unusual chemistry as imposed by the steric restraints of the organometallic ligand provide the impetus for synthesizing new compounds.^{1,2} The (trimethylsilyl)methyl derivatives of the Group III elements, boron,³ aluminum,⁴ and indium¹ have been prepared and fully characterized. The boron derivative,³ $B(CH_2SiMe_3)_3$, is readily made from $BF_3 \cdot O(C_2H_5)_2$ by a standard Grignard reaction in refluxing diethylether solution. Available data suggest that $B(CH_2SiMe_3)_3$ has a trigonal planar structure. The aluminum compound,⁴ $Al(CH_2SiMe_3)_3$, prepared from $Hg(CH_2SiMe_3)_2$ ⁵ and aluminum foil, exists as a mixture of monomeric and dimeric species in benzene solution. Only in the case of indium¹ has a series of (trimethylsilyl)methyl derivatives $In(CH_2SiMe_3)_x - Cl_{3-x}$ ($x = 1, 2, 3$) been studied. The parent compound, $In(CH_2SiMe_3)_3$ prepared by the Grignard reaction, exists as a monomeric three coordinate species. The chloroindium derivatives¹ were prepared from $In(CH_2SiMe_3)_3$ by means of exchange reactions with $InCl_3$ or elimination reactions with HCl . Available data suggest that both the mono- and di-chloroindium derivatives exist as chlorine bridged dimers but $[In(CH_2SiMe_3)Cl_2]_2$ probably has more extensive association in the solid state.¹ It is noteworthy that neither chloroindium compound formed a stable adduct with any base examined in a Lewis acid-base study. The bases included $N(CH_3)_3$, CH_3CN , $O(C_2H_5)_2$, tetrahydrofuran and dimethoxyethane.

An attempt to prepare $Ga(CH_2SiMe_3)_3$ from gallium metal and $Hg(CH_2SiMe_3)_2$ was surprisingly unsuccessful.⁴ Considering the success

of the Grignard reaction for the preparation of the boron³ and indium¹ derivatives and the subsequent ease of removing diethylether from $\text{In}(\text{CH}_2\text{SiMe}_3)_3$, the Grignard reaction of GaCl_3 was investigated. In this paper we report the high yield synthesis of $\text{Ga}(\text{CH}_2\text{SiMe}_3)_3$. The diethylether was very readily removed. Additional experiments lead to the syntheses of a series of neutral organogallium (III) compounds which incorporate the (trimethylsilyl)methyl ligand, $\text{Ga}(\text{CH}_2\text{SiMe}_3)_n\text{X}_{3-n}$ ($\text{X} = \text{Cl}, \text{Br}; n = 1, 2, 3$). All compounds have been fully characterized by elemental analyses, infrared spectra, molecular weight data, solubility properties, ¹H NMR data and Lewis acid-base studies. Our results suggest that the (trimethylsilyl)methyl ligand introduces new chemical properties, reactivities and structures in some of these organogallium (III) compounds.

Experimental

All compounds described in this investigation were extremely oxygen and moisture sensitive and were manipulated in a vacuum line or a purified nitrogen or argon atmosphere. The solvents and reagents were purified by conventional means. New compounds were analyzed for gallium by EDTA titration.⁶ Chlorine and bromine were determined by standard gravimetric procedures.

Synthesis of $\text{Ga}(\text{CH}_2\text{SiMe}_3)_3$:

The compound, $\text{Ga}(\text{CH}_2\text{SiMe}_3)_3$, was prepared from GaCl_3 and the Grignard reagent,⁷ $\text{Me}_3\text{SiCH}_2\text{MgCl}$, in diethylether solution. An argon purged flask, containing 10.000 g (56.796 mmol) GaCl_3 and 200 mL ether, was

equipped with a mechanical stirrer, condenser, dropping funnel, and inert gas bubbler. Then the ether solution of the Grignard reagent (100 mL, 2.16 M) was added dropwise to the GaCl_3 -ether solution over a period of one hour. After addition was complete, the white pasty mixture was stirred for 24 hours at room temperature. Diethylether was then removed by vacuum distillation. The product, $\text{Ga}(\text{CH}_2\text{SiMe}_3)_3$, a colorless mobile liquid at room temperature was distilled from the reaction flask at 120° under high vacuum. The yield of $\text{Ga}(\text{CH}_2\text{SiMe}_3)_3$ was 17.207 g; 51.966 mmol; 91.5% based on GaCl_3 . Analytical and molecular weight data are given in Table II. Typical solvents for $\text{Ga}(\text{CH}_2\text{SiMe}_3)_3$ include n-pentane, benzene, methylene chloride, acetonitrile, and diethylether.

Synthesis of $\text{Ga}(\text{CH}_2\text{SiMe}_3)_2\text{Br}$, $\text{Ga}(\text{CH}_2\text{SiMe}_3)\text{Br}_2$, and $\text{Ga}(\text{CH}_2\text{SiMe}_3)\text{Cl}_2$:

The bromo derivatives and dichloro derivative were prepared from $\text{Ga}(\text{CH}_2\text{SiMe}_3)_3$ by either an exchange reaction with the appropriate gallium trihalide or an elimination reaction with the appropriate hydrogen halide in benzene solution. Different stoichiometries¹ were required for the different products. The procedure for the exchange reaction involved adding a 5.0 mL benzene solution of $\text{Ga}(\text{CH}_2\text{SiMe}_3)_3$ to a mixture of the gallium trihalide and 10 ml of benzene at 25° . The experimental procedure for the elimination reaction was identical to that described for the synthesis of the corresponding indium derivatives.¹ Typical exchange and elimination reactions were run on a 5-10 mmol scale of $\text{Ga}(\text{CH}_2\text{SiMe}_3)_3$ for a period of 12 hours at 25° . Specific synthetic

Table I

Reactions of $\text{Ga}(\text{CH}_2\text{SiMe}_3)_3$ with Gallium Trihalides or Anhydrous Hydrogen Halides^a

Compound	Stoichiometric Ratios of Reagents	Product Purification	% yield $\text{Si}(\text{CH}_3)_4$ (b)	% yield prod. (c)	Melting point °C
$\text{Ga}(\text{CH}_2\text{SiMe}_3)_2\text{Br}$	GaR_3/HBr	Recrystallization from benzene	99.2	94.0	31.0-32.0
	$2\text{GaR}_3/\text{GaBr}_3$	Recrystallization from benzene	-	99.1	
$\text{Ga}(\text{CH}_2\text{SiMe}_3)\text{Br}_2$	$\text{GaR}_3/2\text{HBr}$	Extraction with benzene	99.5	94.2	19.0-21.0
	$\text{GaR}_3/2\text{GaBr}_3$	Extraction with benzene	-	90.0	
$\text{Ga}(\text{CH}_2\text{SiMe}_3)\text{Cl}_2$	$\text{GaR}_3/2\text{HCl}$	Vacuum sublimation-50°	99.6	91.0	48.0-49.0
	$\text{GaR}_3/2\text{GaCl}_3$	Vacuum sublimation-50°	-	94.5	

(a) All reactions were carried out in benzene solution at 25°.

(b) Tetramethylsilane was collected in a -196° trap. The percent yield of $\text{Si}(\text{CH}_3)_4$ is based upon $\text{Ga}(\text{CH}_2\text{SiMe}_3)_3$.

(c) The percent yield of product is based upon $\text{Ga}(\text{CH}_2\text{SiMe}_3)_3$.

Table II

Analytical and Molecular Weight Data for ((Trimethylsilyl)methyl)gallium Compounds

Compound	Gallium Analysis		Halogen Analysis		Formula Weight (g/m)	Molecular Weight Data	
	% Calc	% Found	% Calc	% Found		Calculated Molality(a)	Observed Molecular Weight (g/m)
$\text{Ga}(\text{CH}_2\text{SiMe}_3)_3$	21.04	20.94	-	-	331	0.0918	379
$\text{Ga}(\text{CH}_2\text{SiMe}_3)_2\text{Cl}$	24.96	25.02	12.69	12.65	280	(b)	378
$\text{Ga}(\text{CH}_2\text{SiMe}_3)_2^-$ $\text{Cl} \cdot \text{N}(\text{CH}_3)_3$	20.62	20.56	10.48	10.31	339	0.0902	370
						0.0491	364
$\text{Ga}(\text{CH}_2\text{SiMe}_3)\text{Cl}_2$	30.61	30.52	31.13	31.10	228	0.1591	461
						0.0796	459
$\text{Ga}(\text{CH}_2\text{SiMe}_3)_2\text{Br}$	21.51	21.46	24.65	24.57	324	0.1852	649
						0.1384	648
$\text{Ga}(\text{CH}_2\text{SiMe}_3)\text{Br}_2$	22.03	21.96	50.49	50.35	317	0.1440	631
						0.0894	630

(a) Calculated molality of solution is based upon monomer.

(b) Compound has insufficient solubility in benzene for molecular weight measurements.

conditions, product purification methods, percent yields of tetramethylsilane from elimination reactions, percent yields of ((trimethylsilyl)methyl)gallium-halide compounds, and their respective melting points are given in Table I. Analytical and molecular weight data are given in Table II. Typical solvents for these three organogallium compounds, $\text{Ga}(\text{CH}_2\text{SiMe}_3)_2\text{Br}$, $\text{Ga}(\text{CH}_2\text{SiMe}_3)\text{Br}_2$ and $\text{Ga}(\text{CH}_2\text{SiMe}_3)\text{Cl}_2$, include n-pentane, benzene, methylene chloride, acetonitrile and diethylether.

Synthesis of $\text{Ga}(\text{CH}_2\text{SiMe}_3)_2\text{Cl}$:

The monochloro derivative was prepared by an elimination reaction between $\text{Ga}(\text{CH}_2\text{SiMe}_3)_3$ and hydrogen chloride under carefully controlled experimental conditions. However difficulty was encountered in obtaining reproducible results for this reaction. The following experimental conditions gave the greatest reproducibility and maximum yield of $\text{Ga}(\text{CH}_2\text{SiMe}_3)_2\text{Cl}$.

In a typical reaction 0.1212g (0.3660 mmol) of $\text{Ga}(\text{CH}_2\text{SiMe}_3)_3$ dissolved in 1.0 mL benzene contained in a 20 mL reaction vessel was reacted with a total of 0.0134g (0.367 mmol) of hydrogen chloride. The hydrogen chloride was added in three equimolar portions by vacuum distillation at -196° . After each addition of hydrogen chloride the reaction mixture was warmed to room temperature and stirred for one hour. During this period a white solid precipitated from the solution. After reaction was complete the volatile components were fractionally distilled to yield 0.0320g (0.363 mmol, 99.2% yield) of tetramethylsilane (-196° trap) and benzene (-78° trap). Then, the nonvolatile reaction

products were extracted twice with a 5.0 mL portion of n-pentane. The insoluble component was collected on a small glass frit and identified as $\text{Ga}(\text{CH}_2\text{SiMe}_3)_2\text{Cl}$ (0.0511 g, 0.183 mmol, 50.5% yield). The soluble fraction was a mixture of $\text{Ga}(\text{CH}_2\text{SiMe}_3)\text{Cl}_2$ and unreacted $\text{Ga}(\text{CH}_2\text{SiMe}_3)_3$. The product, $\text{Ga}(\text{CH}_2\text{SiMe}_3)_2\text{Cl}$, a white crystalline solid had a sharp melting point of 159.5-160.0° and was soluble in polar solvents such as methylene chloride, acetonitrile and diethylether but insoluble in benzene and n-pentane. Analytical data are given in Table II.

Synthesis of $\text{Ga}(\text{CH}_2\text{SiMe}_3)_2\text{Cl}\cdot\text{N}(\text{CH}_3)_3$:

The Lewis acid-base adduct, $\text{Ga}(\text{CH}_2\text{SiMe}_3)_2\text{Cl}\cdot\text{N}(\text{CH}_3)_3$, was prepared by an elimination reaction between $\text{Ga}(\text{CH}_2\text{SiMe}_3)_3$ and trimethylamine hydrochloride in benzene. In a typical reaction, 1.1010 g (3.3252 mmol) of $\text{Ga}(\text{CH}_2\text{SiMe}_3)_3$ dissolved in 5.0 ml of benzene was poured through a teflon stopcock under high vacuum at 25° into a reaction flask containing 0.3141 g (3.326 mmol) of doubly sublimed $(\text{CH}_3)_3\text{N}\cdot\text{HCl}$ and 10 ml of benzene. Reaction was observed to proceed by the gradual disappearance of initially insoluble $(\text{CH}_3)_3\text{N}\cdot\text{HCl}$ over a period of two hours. After reaction was complete the volatile components were separated by vacuum distillation to yield 0.2870 g (3.326 mmol, 100% yield) of tetramethylsilane (-196°) and benzene (-78° trap). The crude product was purified by sublimation at 32° to give $\text{Ga}(\text{CH}_2\text{SiMe}_3)_2\text{Cl}\cdot\text{N}(\text{CH}_3)_3$ as a white crystalline solid (1.108 g, 3.276 mmol, 98.5% yield). The purified product had a melting point of 30.0-31.0° and was soluble in n-pentane, benzene, methylene chloride, acetonitrile and diethylether. Analytical and molecular weight data are given in Table II. A compound with identical properties

was prepared by reacting equimolar quantities of $\text{Ga}(\text{CH}_2\text{SiMe}_3)_2\text{Cl}$ and $\text{N}(\text{CH}_3)_3$ at 0° .

Molecular Weight Studies:

Molecular weight measurements were obtained cryoscopically in benzene solution using an instrument similar to that described by Shriver.⁸ Molecular weight data for all compounds are given in Table II.

Infrared Spectra:

The infrared spectra were recorded in the range 4000 to 250 cm^{-1} by means of a Perkin-Elmer Model 457 spectrometer. The spectra were recorded as neat liquids or as Nujol mulls using CsI plates. Absorption intensities were measured using the method of Durkin, Glore, and DeHayes.⁹

Following are the spectral data: frequency, cm^{-1} (intensity: s, strong; m, medium; w, weak; sh, shoulder; vs, very strong). Bands due to mulling agents have been omitted.

$\text{Ga}(\text{CH}_2\text{SiMe}_3)_3$ (neat liquid):

2936 (vs), 2882 (s), 2802 (m), 1441 (m), 1403 (m), 1381 (m), 1354 (m),
1299 (w), 1266 (s), 1251 (vs), 1201 (m), 1130 (w), 990 (s), 957 (s),
860 (vs), 831 (vs), 759 (s), 725 (s), 693 (s), 681 (sh), 535 (m),
512 (m).

$\text{Ga}(\text{CH}_2\text{SiMe}_3)_2\text{Cl}$ (Nujol mull):

1269 (s), 1254 (vs), 1973 (s), 1018 (s), 982 (m), 864 (vs), 835 (vs),
771 (m), 725 (m), 700 (w), 583 (m), 545 (m), 282 (s), 263 (sh).

$\text{Ga}(\text{CH}_2\text{SiMe}_3)_2\text{Cl}\cdot\text{N}(\text{CH}_3)_3$ (Nujol mull):

1265 (s), 1250 (vs), 1112 (w), 995 (s), 975 (s), 861 (vs), 832 (vs),
760 (s), 740 (s), 692 (m), 591 (m), 575 (m), 515 (m), 501 (sh),
278 (s), 262 (sh).

$\text{Ga}(\text{CH}_2\text{SiMe}_3)\text{Cl}_2$ (Nujol mull):

1269 (s), 1252 (vs), 1013 (s), 980 (m), 861 (vs), 832 (vs), 776 (m),
721 (m), 698 (m), 581 (m), 541 (m), 369 (m), 342 (s), 316 (vs).

$\text{Ga}(\text{CH}_2\text{SiMe}_3)_2\text{Br}$ (Nujol mull):

1260 (s), 1253 (vs), 1198 (w), 1110 (s), 978 (m), 850 (vs), 838 (vs),
816 (m), 763 (m), 732 (m), 698 (m), 578 (m), 560 (sh), 548 (m).

$\text{Ga}(\text{CH}_2\text{SiMe}_3)\text{Br}_2$ (Nujol mull):

1262 (s), 1256 (vs), 1105 (s), 978 (m), 860 (vs), 842 (vs), 765 (m),
730 (m), 705 (m), 585 (m), 550 (m).

Proton Nuclear Magnetic Resonance Spectra:

The ^1H NMR spectra were recorded at 100 MHz and ambient temperature using a Jeolco Model MH-100 spectrometer. All chemical shifts (τ) are given in ppm (Table III) and are referenced to tetramethylsilane as 10.00 ppm. The spectra of all ((trimethylsilyl)methyl)gallium compounds were observed as methylene chloride solutions.

Table III

Proton NMR Data for ((Trimethylsilyl)methyl)gallium Compounds and their Lewis Acid-Base Adducts (a)

Lewis Acid	Lewis Base	Si-Me (ppm)	SiCH ₂ (ppm)	Lewis Base protons (ppm)
Ga(CH ₂ SiMe ₃) ₃	—	9.91	10.15	—
"	O(CH ₂) ₄	9.91	10.35	multiplet CH ₂ 6.13
"	N(CH ₃) ₃	9.90	10.68	multiplet CH ₂ 8.05 singlet CH ₃ 7.84
Ga(CH ₂ SiMe ₃) ₂ Cl	—	9.88	9.73	—
"	O(CH ₂) ₄	9.85	10.23	multiplet CH ₂ 6.04 multiplet CH ₂ 7.91
"	N(CH ₃) ₃	9.90	10.42	singlet CH ₃ 7.53
Ga(CH ₂ SiMe ₃)Cl ₂	—	9.88	9.47	—
"	CH ₃ OC ₂ H ₄ OCH ₃	9.85	9.89	singlet CH ₂ 5.95 singlet CH ₃ 6.31
"	O(C ₂ H ₅) ₂	9.85	9.92	quartet CH ₂ 5.83 triplet CH ₃ 8.59
"	CH ₃ CN	9.86	9.94	singlet CH ₃ 7.50
"	O(CH ₂) ₄	9.87	9.97	multiplet CH ₂ 5.81 multiplet CH ₂ 7.89

Table III (continued)

Lewis Acid	Lewis Base	Si-Me (ppm)	SiCH ₂ (ppm)	Lewis Base protons (ppm)
Ga(CH ₂ SiMe ₃)Cl ₂	N(CH ₃) ₃	9.85	10.12	singlet CH ₃ 7.37
Ga(CH ₂ SiMe ₃) ₂ Br	—	9.82	9.59	—
"	O(CH ₂) ₄	9.86	10.08	multiplet CH ₂ 5.93
"	N(CH ₃) ₃	9.86	10.29	multiplet CH ₂ 7.93
Ga(CH ₂ SiMe ₃)Br ₂	—	9.86	9.19	singlet CH ₃ 7.47
"	O(C ₂ H ₅) ₂	9.85	9.73	—
"	CH ₃ OC ₂ H ₄ OCH ₃	9.86	9.74	quartet CH ₂ 5.75
"	CH ₃ CN	9.88	9.78	triplet CH ₃ 8.60
"	O(CH ₂) ₄	9.88	9.80	singlet CH ₂ 5.98
"	N(CH ₃) ₃	9.86	9.98	singlet CH ₃ 6.33
				singlet CH ₃ 7.44
				multiplet CH ₂ 5.61
				multiplet CH ₂ 7.90
				singlet CH ₃ 7.36

(a) The chemical shifts (ppm) for the non-adducted Lewis Base-protons in methylene chloride relative to Si(CH₃)₄ are the following: diethylether, quartet CH₂ (6.58), triplet CH₃ (8.81); dimethoxyethane, singlet CH₂ (6.57), singlet CH₃ (6.72); tetrahydrofuran multiplet α-CH₂ (6.40), multiplet β-CH₂ (8.25); acetonitrile singlet CH₃ (8.05), and trimethylamine singlet CH₃ (7.79).

Lewis Acidity Studies:

The Lewis acidities of the ((trimethylsilyl)methyl)gallium compounds were studied by reacting a stoichiometric quantity of the desired acid with excess base (trimethylamine, acetonitrile, diethyl ether, tetrahydrofuran and dimethoxyethane). The reaction mixture was stirred at room temperature for two hours. The volatile components were then removed by pumping on the sample until no dissociation pressure was observed. If a stoichiometric quantity of base was retained by the acid, the stable adduct was characterized by its ^1H NMR spectrum (Table III). In those cases in which a non-stoichiometric quantity of base was retained, the product was not further characterized.

Stable 1:1 adducts were isolated at room temperatures for the following acid-base pairs: $\text{Ga}(\text{CH}_2\text{SiMe}_3)_3$ - tetrahydrofuran and trimethylamine; $\text{Ga}(\text{CH}_2\text{SiMe}_3)_2\text{Cl}$ - tetrahydrofuran and - trimethylamine; $\text{Ga}(\text{CH}_2\text{SiMe}_3)\text{Cl}_2$ - diethylether, - dimethoxyethane, - acetonitrile, - trimethylamine and - tetrahydrofuran; $\text{Ga}(\text{CH}_2\text{SiMe}_3)_2\text{Br}$ - tetrahydrofuran and - trimethylamine; and $\text{Ga}(\text{CH}_2\text{SiMe}_3)\text{Br}_2$ - diethylether, - dimethoxyethane, - acetonitrile, - trimethylamine and - tetrahydrofuran.

Results and Discussion

A series of neutral organogallium(III) compounds which incorporate the (trimethylsilyl)methyl ligand, $\text{Ga}(\text{CH}_2\text{SiMe}_3)_n \text{X}_{3-n}$ (where $\text{X} = \text{Cl}, \text{Br}; n = 1,2,3$) have been prepared and fully characterized. The elemental analyses, ^1H NMR are infrared spectroscopy, molecular weight data and solubility properties suggest the following molecular formulas:

$\text{Ga}(\text{CH}_2\text{SiMe}_3)_3$, $[\text{Ga}(\text{CH}_2\text{SiMe}_3)_2\text{Cl}]_x$, $[\text{Ga}(\text{CH}_2\text{SiMe}_3)_2\text{Br}]_2$, $[\text{Ga}(\text{CH}_2\text{SiMe}_3)\text{Cl}_2]_2$, and $[\text{Ga}(\text{CH}_2\text{SiMe}_3)\text{Br}_2]_2$. These new organogallium(III) compounds exhibit the high thermal stability expected for (trimethylsilyl)methyl derivatives. It is noteworthy that the (trimethylsilyl)methyl ligand significantly influences the chemistry of $\text{Ga}(\text{CH}_2\text{SiMe}_3)_3$ and $\text{Ga}(\text{CH}_2\text{SiMe}_3)_2\text{Cl}$ when compared with other organogallium compounds. The Lewis acidic behavior of $\text{Ga}(\text{CH}_2\text{SiMe}_3)_3$ has been greatly diminished and the chemical and physical properties of $\text{Ga}(\text{CH}_2\text{SiMe}_3)_2\text{Cl}$ suggest that the compound might have an unusual structure. These changes in chemical behavior contrast the similarities in properties exhibited by related simple organo- and ((trimethylsilyl)methyl)-indium(III) derivatives.¹

The parent compound of the series, $\text{Ga}(\text{CH}_2\text{SiMe}_3)_3$ was readily prepared in 91% yield by a standard Grignard reaction in diethylether solution at room temperature. The best synthetic conditions involved adding a 13% excess of the Grignard reagent to the GaCl_3 in diethylether solution. The product, $\text{Ga}(\text{CH}_2\text{SiMe}_3)_3$, was isolated as a colorless, mobile liquid at room temperature. A significant feature in the preparative scheme is that diethylether is readily separated from $\text{Ga}(\text{CH}_2\text{SiMe}_3)_3$ by vacuum distillation at 25° over a period of three hours. The steric restraints imposed by the bulky (trimethylsilyl)methyl ligand apparently reduce the Lewis acidity of $\text{Ga}(\text{CH}_2\text{SiMe}_3)_3$ compared with other organogallium(III) compounds.^{10,11} The compound, $\text{Ga}(\text{CH}_2\text{SiMe}_3)_3$, like the analogous aluminum compound,⁴ $\text{Al}(\text{CH}_2\text{SiMe}_3)_3$, is spontaneously flammable in air and reacts violently with water. It is of interest that the gallium(III) compound, $\text{Ga}(\text{CH}_2\text{SiMe}_3)_3$, is exceedingly more reactive than

$\text{In}(\text{CH}_2\text{SiMe}_3)_3$.¹ The chemical properties of $\text{Ga}(\text{CH}_2\text{SiMe}_3)_3$ are indicative of a simple three coordinate gallium compound analogous to $\text{Ga}(\text{CH}_3)_3$.¹¹ Cryoscopic molecular weight measurements have shown the compound to exist as a monomeric species in benzene solution. Our infrared data are also fully consistent with this formulation. The asymmetrical Ga-C₃ stretching vibrations give rise to an intense doublet at 535 and 512 cm^{-1} . There were no absorptions observed in the region 510-300 cm^{-1} in which the symmetrical Ga-C₃ vibrations would be expected. This is in full agreement with our proposed three coordinate structure for $\text{Ga}(\text{CH}_2\text{SiMe}_3)_3$ since the symmetrical Ga-C₃ vibrations would be infrared inactive in a planar molecule.¹⁰

The monobromo-, dibromo-, and dichloro-((trimethylsilyl)methyl)-gallium derivatives were readily prepared from $\text{Ga}(\text{CH}_2\text{SiMe}_3)_3$ using stoichiometric quantities of gallium trihalide in an exchange reaction or anhydrous hydrogen halide in an elimination reaction. These reactions have been discussed in detail for the preparation of analogous ((trimethylsilyl)methyl)indium(III)-chloride derivatives.¹ Our available data suggest that these organogallium(III) halide compounds exist as halogen bridged dimers with the following molecular formulas: $[\text{Ga}(\text{CH}_2\text{SiMe}_3)_2\text{Br}]_2$, $[\text{Ga}(\text{CH}_2\text{SiMe}_3)\text{Br}_2]_2$ and $[\text{Ga}(\text{CH}_2\text{SiMe}_2)\text{Cl}_2]_2$. Dimeric species were shown to be present in benzene solution by cryoscopic molecular weight data. The ¹H NMR and infrared data are also fully consistent with these formulations. It is noteworthy that these ((trimethylsilyl)methyl)gallium(III)-halide compounds have properties more similar to those of the corresponding methylgallium halide derivatives^{12,13} than the related higher alkyl species. The compounds of the general

formula R_nGaCl_{3-n} ($R = C_2H_5$ to C_4H_9 isomers; $n = 1,2$) have chlorine bridged dimeric structures and are liquids at room temperature.¹⁴

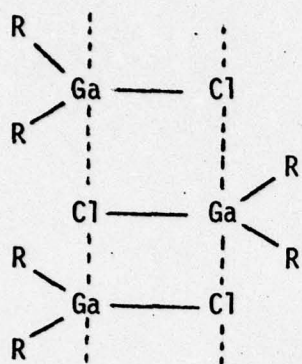
Structural studies have confirmed the chlorine bridged dimeric structures^{15,16} for $[CH_3GaCl_2]_2$ and $[C_6H_5GaCl_2]_2$ which are analogous to that proposed for $[Ga(CH_2SiMe_3)Cl_2]_2$. In contrast the organoindium(III) derivative, $In(CH_2SiMe_3)Cl_2$, is believed to have more extensive association in the solid state.¹ The indium atom is suggested to exist in a strongly distorted trigonal bipyramidal coordination of one (trimethylsilyl)methyl group and four chlorines.

The monochloro-substituted derivative, $Ga(CH_2SiMe_3)_2Cl$, was prepared in surprisingly low yields in comparison to the reactions which gave near quantitative yields of $[Ga(CH_2SiMe_3)_2Br]_2$ and $[In(CH_2SiMe_3)_2Cl]_2$.¹ The best procedure for the preparation of $Ga(CH_2SiMe_3)_2Cl$ involved small scale elimination reactions. Anhydrous hydrogen chloride was added in several equimolar portions to a benzene solution of $Ga(CH_2SiMe_3)_3$. Within one hour a white crystalline solid later identified as $Ga(CH_2SiMe_3)_2Cl$, precipitated from solution. The other products observed from the reaction included $Si(CH_3)_4$, $[Ga(CH_2SiMe_3)Cl_2]_2$ and unreacted $Ga(CH_2SiMe_3)_3$. The elemental analyses, ¹H NMR and infrared data and the quantitative hydrolysis of (trimethylsilyl)methyl groups confirm the formula of the insoluble reaction product as $Ga(CH_2SiMe_3)_2Cl$. The chemical and physical properties of $Ga(CH_2SiMe_3)_2Cl \cdot N(CH_3)_3$ prepared from equimolar quantities of $Ga(CH_2SiMe_3)_2Cl$ and $N(CH_3)_3$ at 0° are identical in every respect with those of $Ga(CH_2SiMe_3)_2Cl \cdot N(CH_3)_3$ prepared from $Ga(CH_2SiMe_3)_3$ and $(CH_3)_3N \cdot HCl$. All data suggest that the low

yields of $\text{Ga}(\text{CH}_2\text{SiMe}_3)_2\text{Cl}$ from the elimination reaction are related to further reaction. Unless $\text{Ga}(\text{CH}_2\text{SiMe}_3)_2\text{Cl}$ precipitates from solution, it reacts with a second mole of HCl to give $\text{Ga}(\text{CH}_2\text{SiMe}_3)\text{Cl}_2$. The ^1H NMR spectrum of $\text{Ga}(\text{CH}_2\text{SiMe}_3)_2\text{Cl}$ in CH_2Cl_2 solution suggests that $\text{Ga}(\text{CH}_2\text{SiMe}_3)_2\text{Cl}$ does not disproportionate to give the observed products of the preparative reaction.

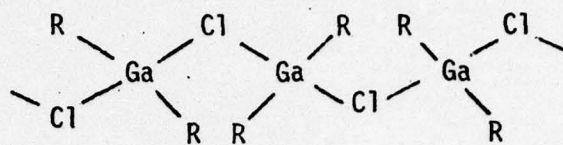
Various reaction conditions were attempted to maximize the yield of $\text{Ga}(\text{CH}_2\text{SiMe}_3)_2\text{Cl}$ and increase the reproducibility of the reaction. Elimination reactions at low temperature (0° , -46° , -78°) using toluene as solvent or reactions at 25° in methylene chloride, diethylether, acetonitrile, or toluene gave decreased yields of $\text{Ga}(\text{CH}_2\text{SiMe}_3)_2\text{Cl}$. The exchange reaction between $\text{Ga}(\text{CH}_2\text{SiMe}_3)_3$ and GaCl_3 in benzene solution gave none of the desired product, $\text{Ga}(\text{CH}_2\text{SiMe}_3)_2\text{Cl}$. The monochloro derivative could not be isolated from a reaction mixture of GaCl_3 with two moles of the Grignard reagent, $\text{Me}_3\text{SiCH}_2\text{MgCl}$, in ether solution.

The unusual chemical and physical properties of $\text{Ga}(\text{CH}_2\text{SiMe}_3)_2\text{Cl}$ when compared with other monohalogallium derivatives suggest a unique structure probably involving extensive association of monomeric units in the solid state as shown in the following type of polymeric structures.



I

"Ladder polymer"



II

Linear polymer

Structure I would minimize interactions between the (trimethylsilyl)methyl groups and maximize the coordination number of the gallium. The gallium atom would have severely distorted trigonal bipyramidal coordination. Structure II would have the normal coordination number four around gallium but interactions between (trimethylsilyl)methyl groups would be greater than in Structure I. Simple dimeric and monomeric structures as well as ion pair formulations are ruled out on the basis of chemical, physical and spectral data. The high melting point, non-volatile behavior up to 160° and the limited solubility of $\text{Ga}(\text{CH}_2\text{SiMe}_3)_2\text{Cl}$ in benzene or pentane are in sharp contrast with all other organogallium halogen compounds,^{12,14} including $[\text{Ga}(\text{CH}_2\text{SiMe}_3)_2\text{Br}]_2$. All dimeric compounds of the general formula¹⁴ $[\text{GaR}_n\text{Cl}_{3-n}]_2$, where $\text{R} = \text{CH}_3$ to C_4H_9 isomers; $n = 1, 2$, are volatile, low melting solids or liquids at room temperature. All of these compounds are also soluble in non-polar solvents such as benzene or pentane. Even, $[\text{Ga}(\text{CH}_2\text{SiMe}_3)_2\text{Br}]_2$, $[\text{Ga}(\text{CH}_2\text{SiMe}_3)\text{Br}]_2$ and $[\text{Ga}(\text{CH}_2\text{SiMe}_3)\text{Cl}]_2$ have low melting points and are soluble in non-polar solvents. Thus, $\text{Ga}(\text{CH}_2\text{SiMe}_3)_2\text{Cl}$ is the only organogallium(III) chlorine compound which is not dimeric.

The infrared spectral data (Table IV) support the proposed dimeric structures for $[\text{Ga}(\text{CH}_2\text{SiMe}_3)_2\text{Br}]_2$, $[\text{Ga}(\text{CH}_2\text{SiMe}_3)\text{Br}_2]_2$ and $[\text{Ga}(\text{CH}_2\text{SiMe}_3)\text{Cl}_2]_2$, as well as a unique structure, possibly a "ladder polymer" for $[\text{Ga}(\text{CH}_2\text{SiMe}_3)_2\text{Cl}]_x$. The frequencies of the gallium-carbon and gallium-halogen vibrations are directly related to the structural backbones of the compound. All compounds have two absorptions assigned to gallium-carbon vibrations. The dimeric methylgallium compounds, $[(\text{CH}_3)_2\text{GaCl}]_2$ and $[\text{CH}_3\text{GaCl}_2]_2$, also have two $\nu\text{Ga-C}$ absorptions at frequencies similar to those observed for the corresponding (trimethylsilyl)methyl derivatives. The dichlorogallium compounds, $[\text{Ga}(\text{CH}_2\text{SiMe}_3)\text{Cl}_2]_2$ and $[\text{CH}_3\text{GaCl}_2]_2$ also have similar $\nu\text{Ga-Cl}$ absorptions, indicative of similar structures. In contrast, the infrared spectra of $\text{Ga}(\text{CH}_2\text{SiMe}_3)_2\text{Cl}$ and $[(\text{CH}_3)_2\text{GaCl}]_2$ are very different which is indicative of different structures. A unique structure is proposed for $\text{Ga}(\text{CH}_2\text{SiMe}_3)_2\text{Cl}$. The dimer $[(\text{CH}_3)_2\text{GaCl}]_2$ has three Ga-Cl bands whereas $\text{Ga}(\text{CH}_2\text{SiMe}_3)_2\text{Cl}$ has one very intense band at 282 cm^{-1} with a shoulder at 263 cm^{-1} . The intensity of the Ga-Cl band is consistent with the proposed arrangement of groups around gallium in the "ladder" polymer. The high coordination number of gallium in the proposed "ladder polymer" could lead to the relatively low frequency observed for the band. The two Ga-C absorptions are consistent with an angular arrangement of (trimethylsilyl)methyl groups and discount a linear symmetry which might occur in an ionic type structure.¹⁷

Lewis acidity studies indicate the following order of increasing acid strength for ((trimethylsilyl)methyl)gallium(III) compounds:

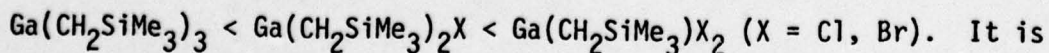


Table IV

Infrared Spectra of ((Trimethylsilyl)methyl)gallium and Methylgallium Compounds^a

Compound	$\nu_{\text{Ga-C}}$ (cm^{-1})	$\nu_{\text{Ga-Cl}}$ (cm^{-1})
$\text{Ga}(\text{CH}_2\text{SiMe}_3)_3$	535(m), 512(m)	-
$\text{Ga}(\text{CH}_2\text{SiMe}_3)_2\text{Cl}$	583(m), 545(m)	282(vs), 263(sh)
$\text{Ga}(\text{CH}_2\text{SiMe}_3)\text{Cl}_2$	581(m), 541(m)	369(m), 342(s), 316(vs)
$\text{Ga}(\text{CH}_2\text{SiMe}_3)_2\text{Br}$	578(m), 548(m)	b
$\text{Ga}(\text{CH}_2\text{SiMe}_3)\text{Br}_2$	585(m), 550(m)	b
$\text{Ga}(\text{CH}_3)_2\text{Cl}$	588(s), 540(m)	335(m), 292(s), 270(vs)
$\text{Ga}(\text{CH}_3)\text{Cl}_2$	586(s), 540(m)	361(vs), 335(vs), 311(m)

- a. Spectra observed as neat liquids or Nujol mulls
- b. Absorption due to Ga-Br vibrations occur at frequencies below the range of our instrument.

of interest that the chloro and bromo compounds showed very similar Lewis acidic behavior. This order is indicated by the range of bases which formed stable adducts at room temperature with a given acid and by relative ^1H NMR chemical shift data (Table III). The Lewis bases studied included diethylether, dimethoxyethane, acetonitrile, tetrahydrofuran and trimethylamine. The weakest Lewis acid of the series is $\text{Ga}(\text{CH}_2\text{SiMe}_3)_3$. It formed stable 1:1 adducts with only trimethylamine, and tetrahydrofuran, the strongest bases. Our experimental data suggest that the diethylether complex is extensively dissociated at 25° . Diethylether could be removed from $\text{Ga}(\text{CH}_2\text{SiMe}_3)_3$ by vacuum distillation at 25° in only 3 hrs. In contrast, diethylether cannot be removed from $\text{Ga}(\text{CH}_3)_3$ at room temperature.¹⁰ The $(\text{CH}_3)_3\text{GaO}(\text{C}_2\text{H}_5)_2$ complex is only extensively dissociated in the vapor phase.¹⁰ The monohaloderivatives, $\text{Ga}(\text{CH}_2\text{SiMe}_3)_2\text{Cl}$ and $\text{Ga}(\text{CH}_2\text{SiMe}_3)_2\text{Br}$, also formed stable 1:1 adducts with only trimethylamine and tetrahydrofuran. However, the ease with which diethylether can be removed from these acids would suggest that they are slightly stronger acids than $\text{Ga}(\text{CH}_2\text{SiMe}_3)_3$. There are no available data which permit a clear distinction between the Lewis acidities of $\text{Ga}(\text{CH}_2\text{SiMe}_3)_2\text{Cl}$ and $\text{Ga}(\text{CH}_2\text{SiMe}_3)_2\text{Br}$. In contrast to the limited number of stable adducts observed for $\text{Ga}(\text{CH}_2\text{SiMe}_3)_3$ and $\text{Ga}(\text{CH}_2\text{SiMe}_3)_2\text{X}$ ($\text{X} = \text{Cl}, \text{Br}$), the dihaloderivatives formed stable 1:1 adducts with all bases studied. The ^1H NMR chemical shift data of all stable adducts compared to the free acid are consistent with the previously observed order of Lewis acidity.

The studies¹ of the interactions of the ((trimethylsilyl)methyl)-indium(III) compounds with an identical range of Lewis bases gave

significantly different results than those observed for the gallium(III) compounds. The strongest Lewis acid of the indium series¹ is $\text{In}(\text{CH}_2\text{SiMe}_3)_3$. It formed a stable 1:1 adduct with only trimethylamine. The compound $(\text{In}(\text{CH}_2\text{SiMe}_3)_2\text{Cl})_2$ did not exhibit any acidic properties whereas $[\text{In}(\text{CH}_2\text{SiMe}_3)\text{Cl}_2]_2$ formed weak adducts with appreciable dissociation pressures.

All data indicate the Lewis acidities of ((trimethylsilyl)methyl)-gallium(III) compounds increase with increasing halogen substitution at gallium. The steric interactions between two (trimethylsilyl)methyl groups is most likely the controlling factor. The weakly acidic properties of $\text{Ga}(\text{CH}_2\text{SiMe}_3)_3$ enable the compound to be synthesized from GaCl_3 and the Grignard reagent in diethylether solution. Furthermore, the steric interactions between the two (trimethylsilyl)methyl groups of $\text{Ga}(\text{CH}_2\text{SiMe}_3)_2\text{Cl}$ might be responsible for preventing dimer formation. The tendency for coordination saturation about gallium would lead to the proposed polymeric type of structures. The dimer, $[\text{Ga}(\text{CH}_2\text{SiMe}_3)_2\text{Br}]_2$, might be stable because the longer gallium-bromine bridge bonds allow a greater distance to be maintained between (trimethylsilyl)methyl groups. It is apparent that as the radius of the central atom decreases from indium to gallium, the (trimethylsilyl)methyl groups introduce unusual changes in the chemistry.

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